

LBSS139WT1G

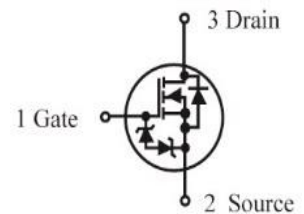
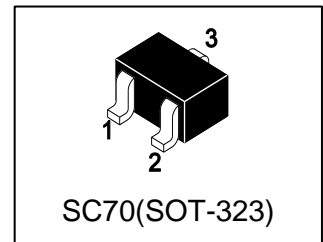
S-LBSS139WT1G

Power MOSFET

200 mAmps, 50 Volts N-Channel SC-70

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low threshold voltage ($V_{GS(th)}$: 0.5V...1.5V) makes it ideal for low voltage applications.
- ESD Protected:1500V



2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBSS139WT1G	J2	3000/Tape&Reel
LBSS139WT3G	J2	10000/Tape&Reel

3. MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DSS}	50	Vdc
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	Vdc
Drain Current			mAdc
– Continuous $T_A = 25^\circ\text{C}$	I_D	200	
– Pulsed ($t_p \leq 10\mu\text{s}$)	I_{DM}	800	

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-4 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	PD	150	mW
		1.2	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient(Note 1)	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction and Storage temperature	T_J, T_{stg}	$-55 \sim +150$	$^\circ\text{C}$
Maximum Lead Temperature for Solde Purposes, for 10 seconds	TL	260	$^\circ\text{C}$

1. FR-4 = 1.0×0.75×0.062 in.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)
OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain–Source Breakdown Voltage (VGS = 0, ID = 250 μ A _{dc})	VBRDSS	50	-	-	V _{dc}
Zero Gate Voltage Drain Current (VGS = 0, VDS = 25 V _{dc}) (VGS = 0, VDS = 50 V _{dc})	IDSS	-	-	0.1 0.5	μ A _{dc}
Gate–Body Leakage Current, Forward (VGS = 20 V _{dc})	IGSSF	-	-	10	μ A _{dc}
Gate–Body Leakage Current, Reverse (VGS = - 20 V _{dc})	IGSSR	-	-	-10	μ A _{dc}

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage (VDS = VGS, ID = 1.0mA _{dc})	VGS(th)	0.5	-	1.5	V _{dc}
Static Drain–Source On–State Resistance (VGS = 2.75 V _{dc} , ID < 200 mA _{dc} , TA = -40°C to +85°C) (VGS = 5.0 V _{dc} , ID = 200 mA _{dc})	RDS(on)	-	5.6	10 3.5	Ohms
Forward Transconductance (VDS = 25 V _{dc} , ID = 200 mA _{dc} , f = 1.0 kHz)	gfs	100	-	-	mS

DYNAMIC CHARACTERISTICS

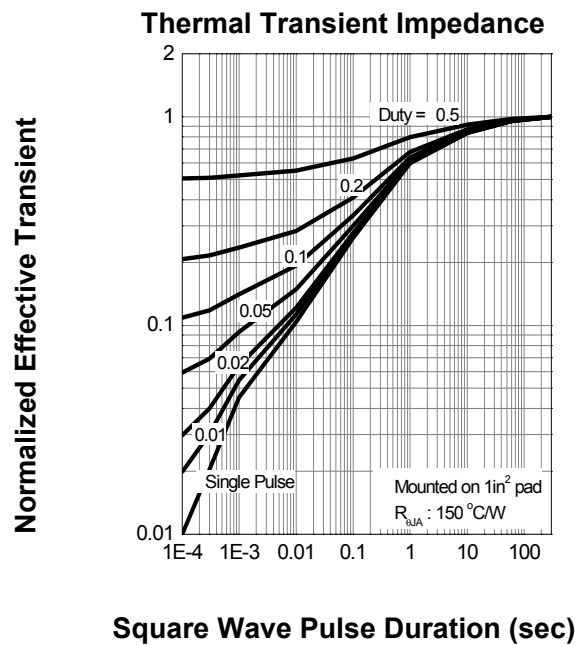
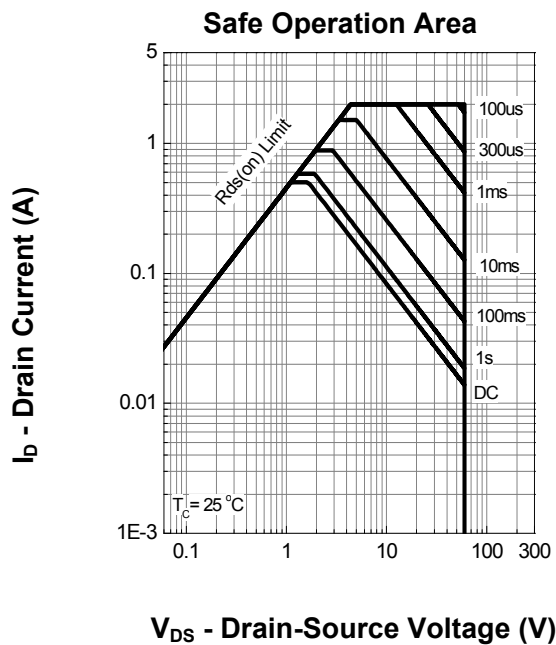
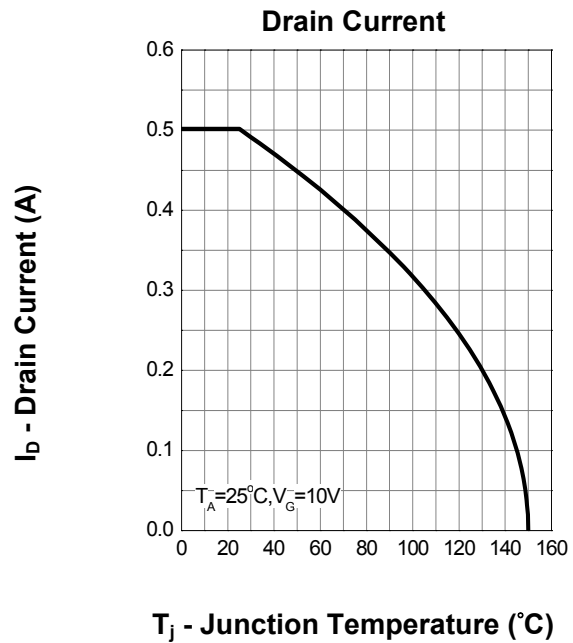
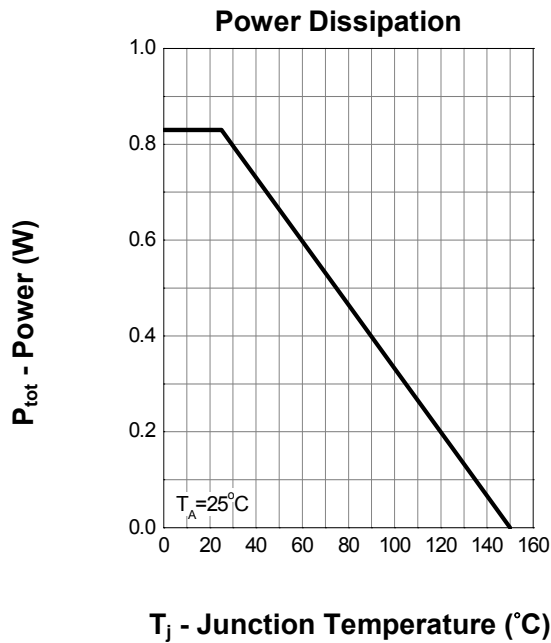
Input Capacitance (VDS = 25 V _{dc} , VGS = 0, f = 1.0 MHz)	Ciss	-	22.8	-	pF
Output Capacitance (VDS = 25 V _{dc} , VGS = 0, f = 1.0 MHz)	Coss	-	3.5	-	pF
Reverse Transfer Capacitance (VDS = 25 V _{dc} , VGS = 0, f = 1.0 MHz)	Crss	-	2.9	-	pF

SWITCHING CHARACTERISTICS

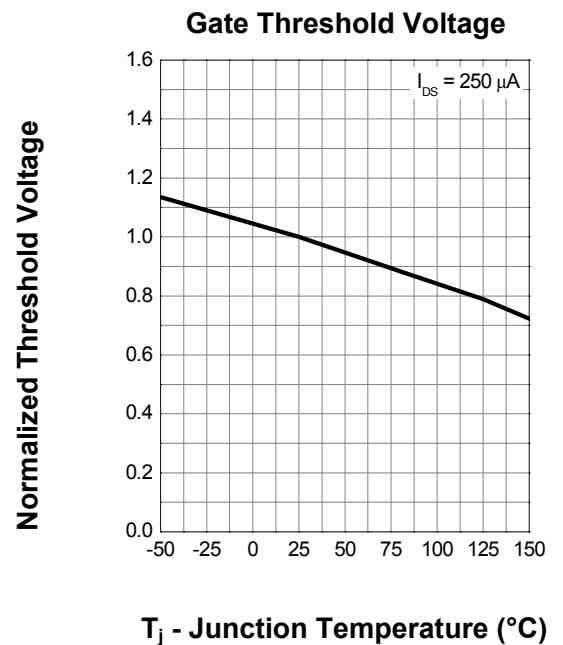
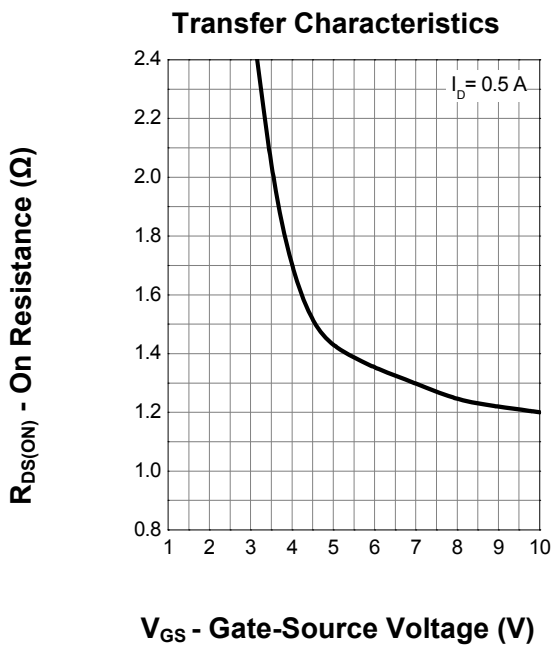
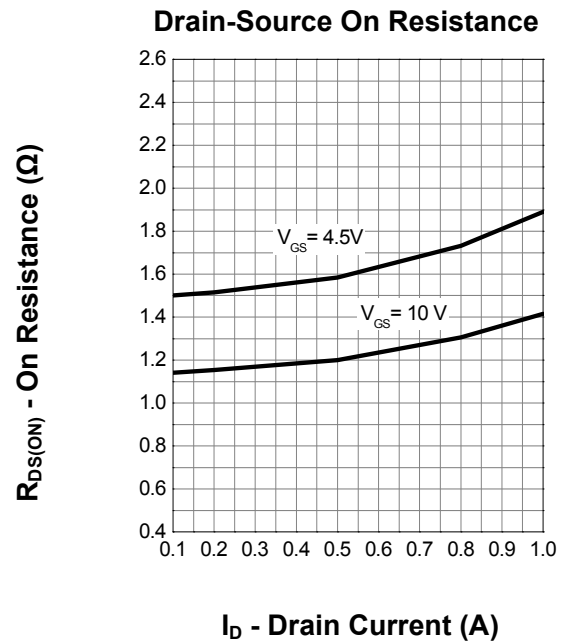
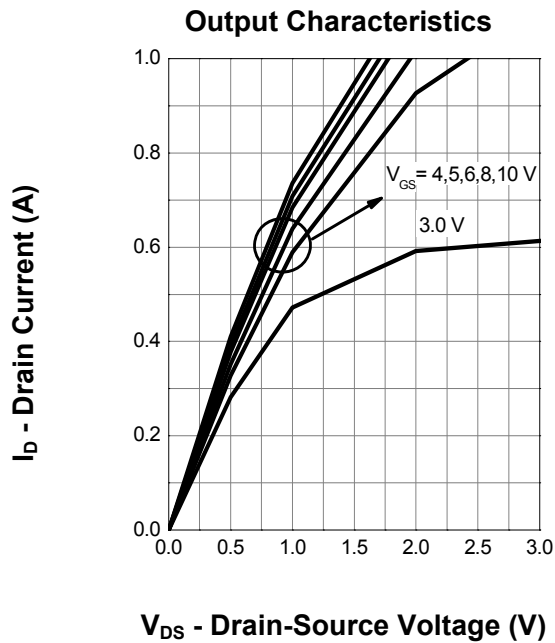
Turn-On Delay Time	(VDD = 30 V _{dc} , VGEN = 10 V, RG = 25 Ω , RL = 60 Ω , ID = 500 mA _{dc})	td(on)	-	3.8	-	ns
Turn-Off Delay Time		td(off)	-	19	-	

 2.Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

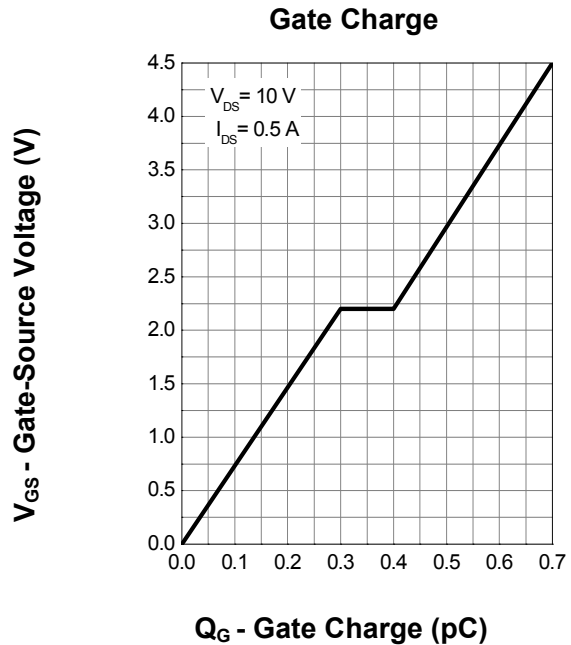
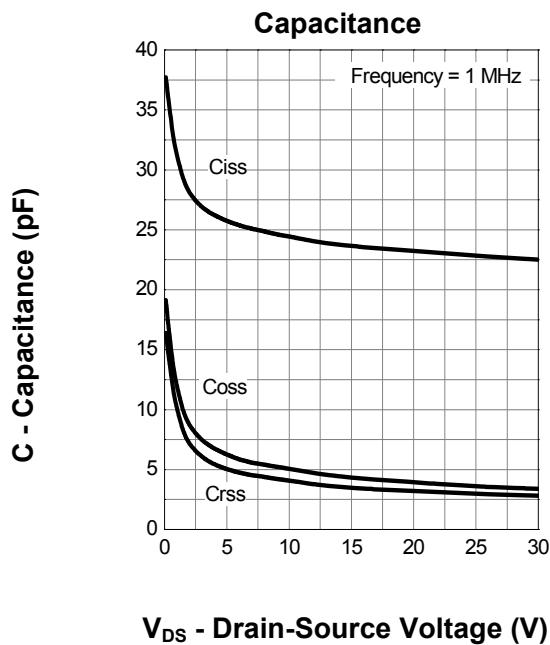
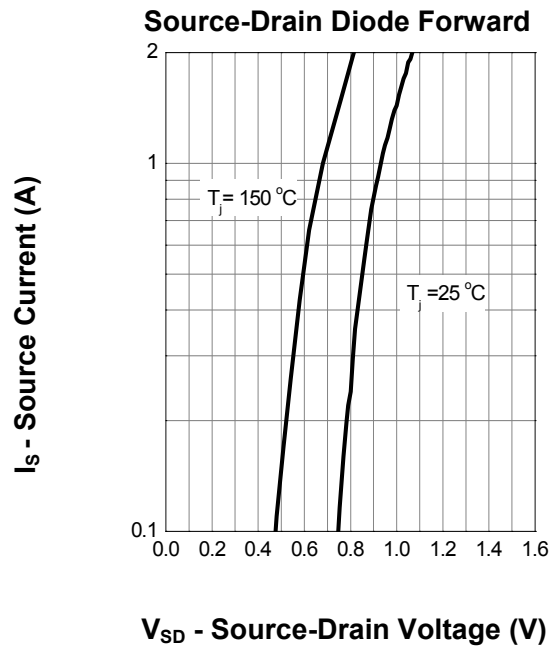
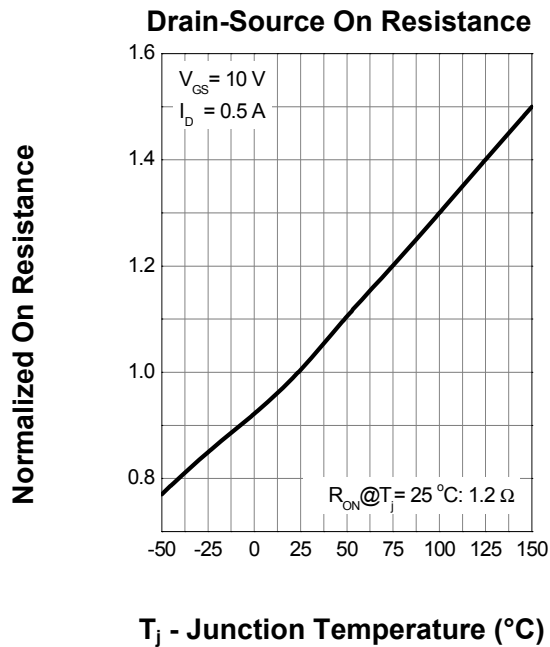
6. ELECTRICAL CHARACTERISTICS CURVES



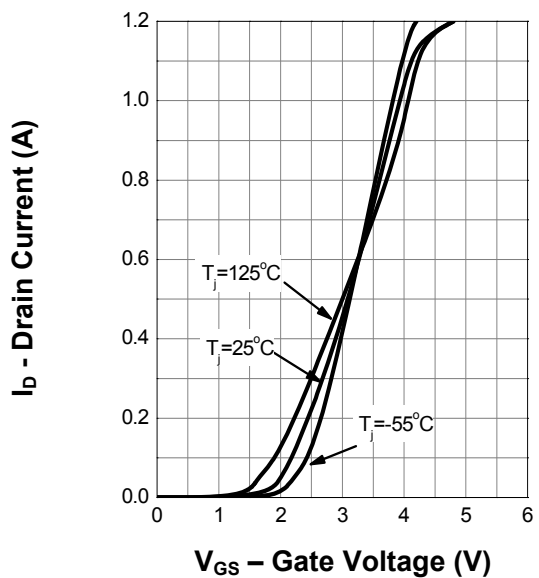
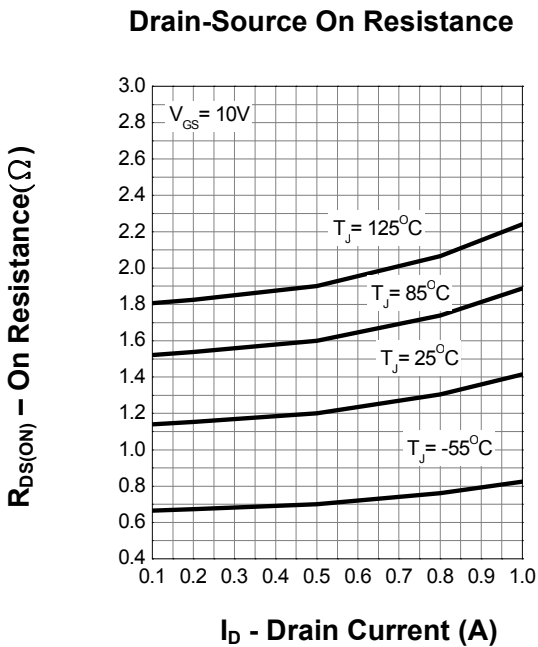
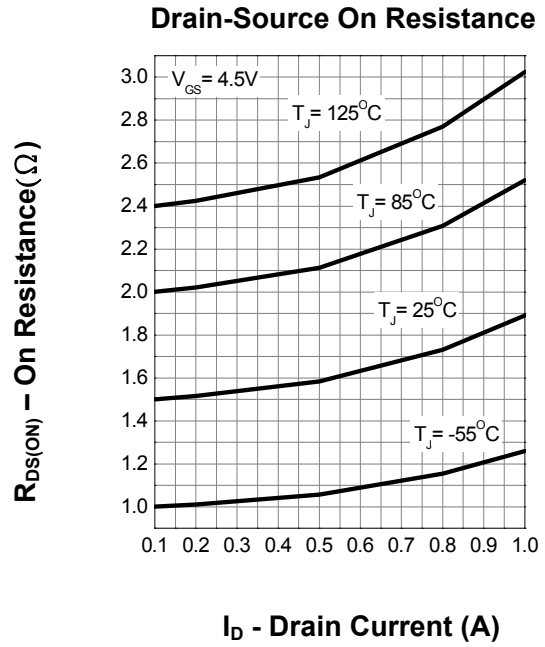
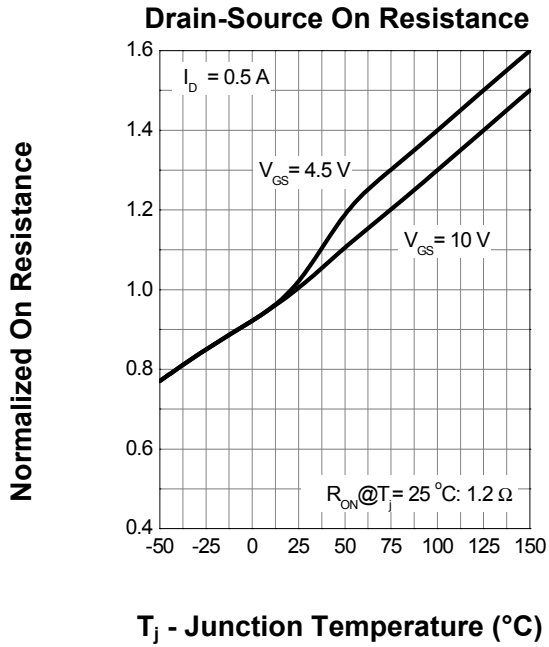
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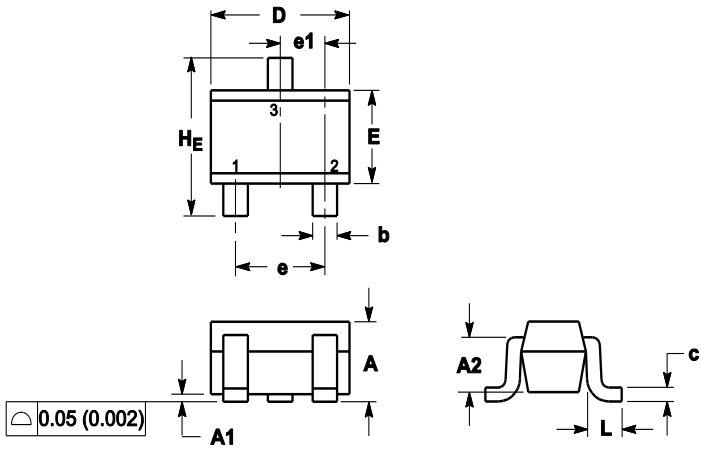


7.OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70REF			0.028REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65REF			0.026REF		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095



8.SOLDERING FOOTPRINT

